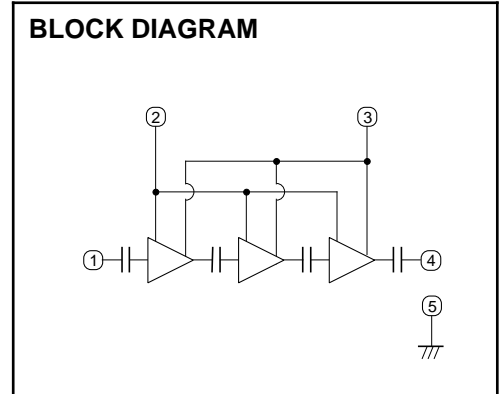
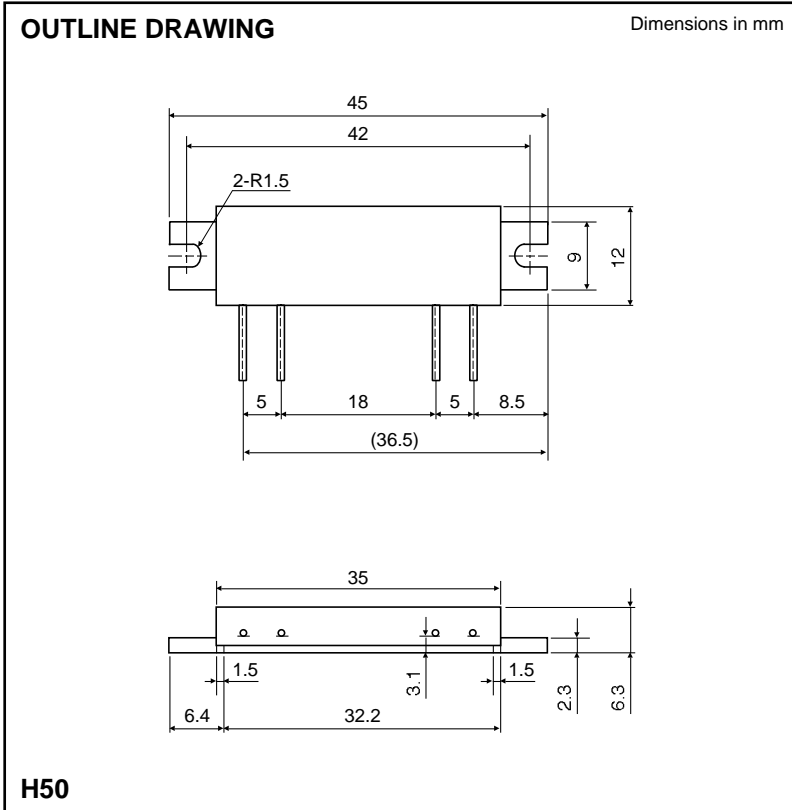


MITSUBISHI RF POWER MODULE
M68745L

SILICON MOS FET POWER AMPLIFIER, 806-870MHz, 3.8W, FM PORTABLE RADIO



PIN:
 ① Pin : RF INPUT
 ② VGG : GATE BIAS SUPPLY
 ③ VDD : DRAIN BIAS SUPPLY
 ④ Po : RF OUTPUT
 ⑤ GND: FIN

ABSOLUTE MAXIMUM RATINGS (Tc=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
VDD	Supply voltage	ZG=ZL=50	9	V
VGG	Gate bias voltage		5.5	V
Pin	Input power	f=806-870MHz, ZG=ZL=50	6	mW
Po	Output power	f=806-870MHz, ZG=ZL=50	6	W
Tc (OP)	Operation case temperature	f=806-870MHz, ZG=ZL=50	-30 to +100	°C
Tstg	Storage temperature		-40 to +100	°C

Note. Above parameters are guaranteed independently.

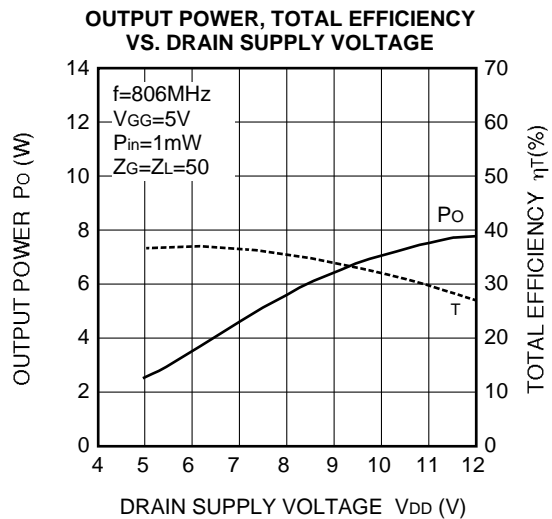
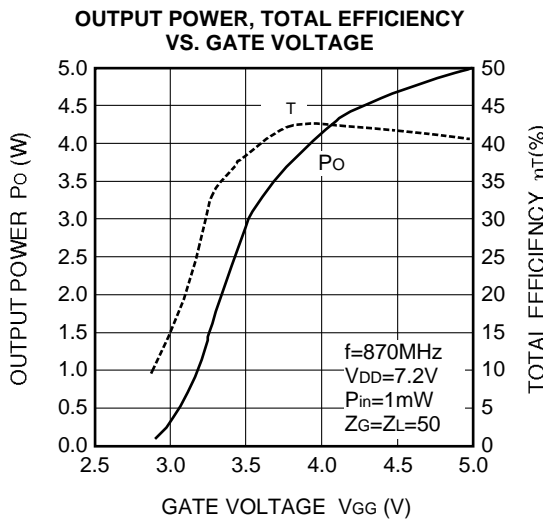
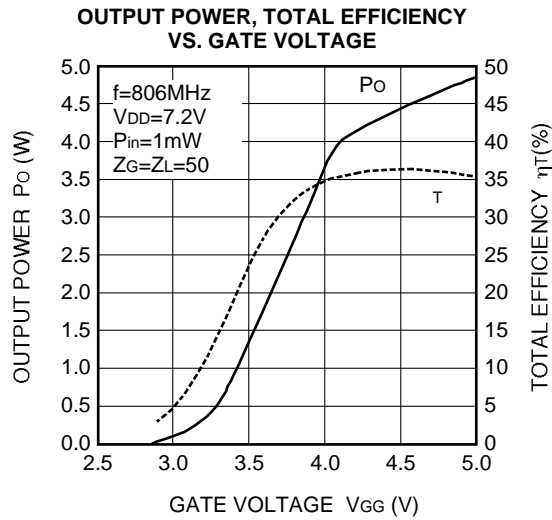
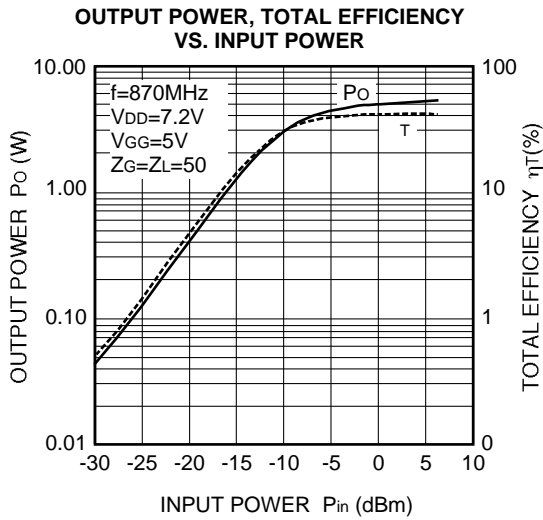
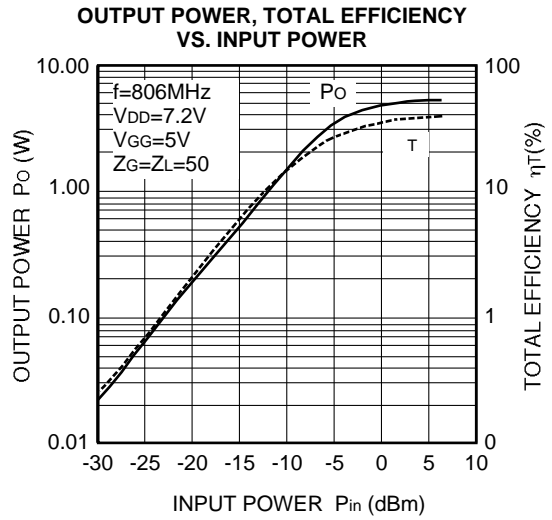
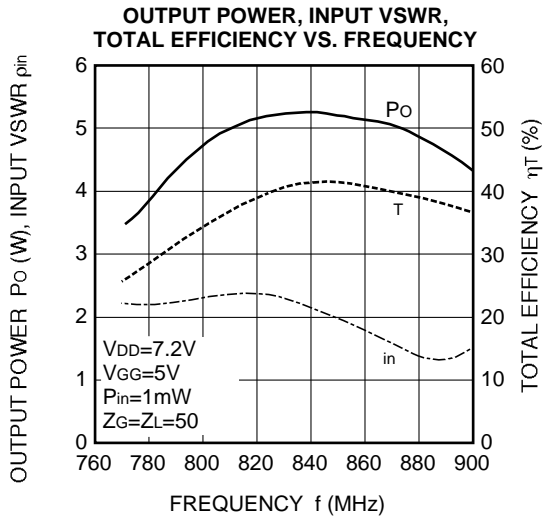
ELECTRICAL CHARACTERISTICS (Tc=25°C, ZG=ZL=50 unless otherwise noted)

Symbol	Parameter	Test conditions	Limits		Unit
			Min	Max	
f	Frequency range		806	870	MHz
Po	Output power	VDD=7.2V, VGG=5V, Pin=1mW, ZG=ZL=50	3.8		W
2fo	2nd. harmonic			-30	dBc
in	Input VSWR			4	—
τ	Total efficiency	PO=3.8W(VGG=Adjust), VDD=7.2V, Pin=1mW, ZG=ZL=50	30		%
—	Stability	ZG=ZL=50, VDD=5-9.3V, Load VSWR <4:1	No parasitic oscillation		—
—	Load VSWR tolerance	VDD=9V, Pin=1mW, PO=3.8W (VGG Adjust), ZL=20:1	No degradation or destroy		—

Note. Above parameters, ratings, limits and test conditions are subject to change.

SILICON MOS FET POWER AMPLIFIER, 806-870MHz, 3.8W, FM PORTABLE RADIO

TYPICAL PERFORMANCE DATA



SILICON MOS FET POWER AMPLIFIER, 806-870MHz, 3.8W, FM PORTABLE RADIO

